

ABSTRACT

A method for forming a die on a wafer is provided. The method includes forming on a wafer a die having an active portion that includes integrated circuitry. The method further includes forming at least one input bond pad on the active portion and at least one test pad on the die. A conductive path is formed between the input bond pad and the test pad. A portion of the conductive path is formed on the die outside of the active portion of the die.

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